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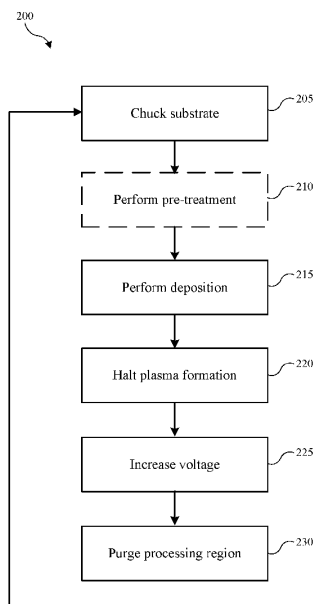


FIG. 2

(57) Abstract: Exemplary deposition methods may include electrostatically chucking a semiconductor substrate at a first voltage within a processing region of a semiconductor processing chamber. The methods may include performing a deposition process. The deposition process may include forming a plasma within the processing region of the semiconductor processing chamber. The methods may include halting formation of the plasma within the semiconductor processing chamber. The methods may include, simultaneously with the halting, increasing the first voltage of electrostatic chucking to a second voltage. The methods may include purging the processing region of the semiconductor processing chamber.

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